

L Number	Hits	Search Text	DB	Time stamp
1	2844187	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:11
2	4924	(memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:14
3	2	((memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacitor) and program\$5 with (cell or element) with (vdd/2 or vcc/2)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:16
4	6650	(memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:16
5	2	((memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacit\$5) and program\$5 with (cell or element) with (vdd/2 or vcc/2)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:17

L Number	Hits	Search Text	DB	Time stamp
1	2844187	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 15:56
2	1229	((memory or storage) and (writ\$6 or program\$6) with (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bit line or digit adj line or conductor) with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:00
4	3	((memory or storage) and (writ\$6 or program\$6) with (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bit line or digit adj line or conductor) with capacitor) and programmable with resistance with (cell or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:08
5	5	((memory or storage) and (writ\$6 or program\$6) with (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bit line or digit adj line or conductor) with capacitor) and program\$5 with resistance with (cell or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:05
6	2739	((memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacitor with (voltage or potential or level)) and programmable with resistance with (cell or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:07
7	7	((memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with capacitor with (voltage or potential or level)) and programmable with resistance with (cell or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/06 16:08